



Sheet 1 of 2

Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 30848/40704	Serial No. 10/516,384
<b>INFORMATION DISCLOSURE STATEMENT</b>			
Applicant Gogolides et al.		Filing Date May 30, 2003	Group

## U.S. PATENT DOCUMENTS

U.S. PATENT DOCUMENTS						
*Examiner Initials	Document Number	Issue Date	Name	Class	Subclass	Filing Date if Appropriate
SJL	2001/0018486A1	08/30/01	Lichtenhan et al.	524	588	
	6,391,471 B1	05/21/02	Hiraoka et al.	428	623	
↓	2003/0022102 A1	01/30/03	Hiraoka et al.	430	270.1	03/07/02

## FOREIGN PATENT DOCUMENTS



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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
SJL		"Double Layer Resist System for High Resolution Lithography", Hatzakis et al., Proc. Microcircuit Engnrg. Lausanne, 1981, pp. 386-396
		"Linear Hybrid Polymer Building Blocks: Methacrylate-Functionalized Polyhedral Oligomeric Silsesquioxane Monomers and Polymers", Lichtenhan et al., Macromolecules 28, 1995, pp. 8435-8437
		"Extension of 248 nm Optical Lithography: A Thin Film Imaging Approach", Lin et al., SPIE Vol. 3333, 1998, pp. 278-288
		"Outlook for 157-nm Resist Design", Kunz et al., SPIE Vol. 3678, March 1999, pp. 13-20
		"Incorporation of Polyhedral Oligosilsesquioxane in Chemically Amplified Resists to Improve Their Reactive Ion Etching Resistance", Wu et al., J. Vac. Sci. Technol. B 19(3), May/June 2001, pp. 851-855
		"Novel CA Resists with Photoacid Generator in Polymer Chain", Wu et al., SPIE Vol. 4345, 2001, pp. 521-527
		"Novel Positive-Tone Chemically Amplified Resists with Photoacid Generator in the Polymer Chains", Wu et al., Adv. Mater 13, No. 9, May 2001, pp. 670-672
		"Silicon-Containing Resists for 157 nm Applications", Sooriyakumaran et al., SPIE Vol. 4345, 2001, pp. 319-326
		"Recent Advances in Resists for 157 nm Microlithography", Trinque et al., J. Vac. Sci. Technol. B 20(2), March/April 2002, pp. 531-536
↓		International Search Report in PCT/GB03/00018 dated September 23, 2003

Examiner	<i>S. J. Lee</i>	Date Considered	<i>9-30-07</i>
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.